

A Product Line of **Diodes Incorporated**

Top View

TSOT25

BKVYW

Top View

DFN 2x2 6L

₹ž

VIN 1

GND 2

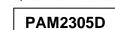
EN 3

NC

ΕN

VIN

Pin Assignments



1A STEP-DOWN DC-DC CONVERTER

5 SW

4_{FB}

6

5

4

Top View

QFN 3x3 16L

sw sw

16 15 14 13

P2305D

XXXYW

5 6 7 8

NEN 2NG

•

2

4

GND 1

GND 2

GND

FB

FB

GND

SW

VIN 12

VIN 9

VIN

11 VIN

10

Description

The PAM2305D is a step-down current-mode, DC-DC converter. At heavy load, the constant frequency PWM control per forms excellent stability and transient response. To ensure the longest battery life in portable applications, the PAM2305D provides a power-saving Pulse-Skipping Modulation (PSM) mode to reduce quiescent current under light load operation to save power.

The PAM2305D supports a range of input voltages from 2.5V to 5.5V, allowing the use of a single Li+/Li-polymer cell, multiple Alkaline/NiMH cell, USB, and other standard power sources. The output voltage is adjustable from 0.6V to the input voltage. All versions employ internal power switch and synchronous rectifier to minimize external part count and realize high efficiency. During shutdown, the input is disconnected from the output and the shutdown current is less than 0.1µA. Other key features include under-voltage lockout to prevent deep battery discharge.

The PAM2305D is available in TSOT25, DFN2x2-6 Pin and QFN3x3-16 Pin packages.

Features

- Efficiency up to 96% •
- Only 40µA (typ) Quiescent Current •
- Output Current: Up to 1A
- Internal Synchronous Rectifier
- 1.5MHz Switching Frequency •
- Soft Start
- Under-Voltage Lockout
- Short Circuit Protection
- Thermal Shutdown
- 5-pin Small TSOT25, DFN2x2-6 Pin and QFN3x3-16 Pin Packages
- Pb-Free Packages

Applications

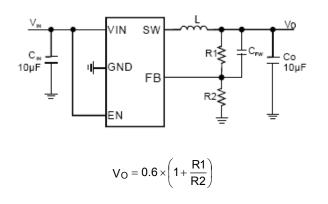
- Cellular Phone
- **Portable Electronics**
- Wireless Devices
- Cordless Phone
- **Computer Peripherals**
- **Battery Powered Widgets** .
- **Electronic Scales**
- **Digital Frame**

PAM2305D





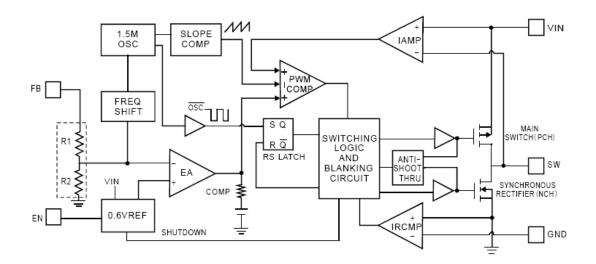
Typical Applications Circuit



Pin Descriptions

Pin Package Name		ne	Function	
Name	TSOT25	DFN2x2-6L	QFN3x3-16L	Function
VIN	1	3	9, 10, 11, 12	Chip main power supply pin.
GND	2	5	1, 2, 3, 5	Ground.
EN	3	2	7	Enable Control Input. Force this pin voltage above 1.5V, enables the chip, and below 0.3V shuts down the device.
FB	4	6	4	Feedback voltage to internal error amplifier, the threshold voltage is 0.6V.
SW	5	4	13, 14, 15	The drains of the internal main and synchronous power MOSFET.
NC	_	1	6, 8, 16	No connection.

Functional Block Diagram





Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

These are stress ratings only and functional operation is not implied. Exposure to absolute maximum ratings for prolonged time periods may affect device reliability. All voltages are with respect to ground.

Parameter	Rating	Unit
Input Voltage	-0.3 to +6.0	V
EN, FB Pin Voltage	-0.3 to V _{IN}	V
SW Pin Voltage	-0.3 to (V _{IN} +0.3)	V
Junction Temperature	150	°C
Storage Temperature Range	-65 to +150	°C
Soldering Temperature	300, 5sec	°C

Recommended Operating Conditions (@T_A = +25°C, unless otherwise specified.)

Parameter	Rating	Unit
Supply Voltage	2.5 to 5.5	V
Operation Temperature Range	-40 to +85	°C
Junction Temperature Range	-40 to +125	C

Thermal Information

Parameter	Package	Symbol	Max	Unit
	TSOT25 (Note 1)		130	°C/W
Thermal Resistance (Junction to Case)	DFN2x2-6	θ _{JC}	25	
	QFN3x3-16		14	
	TSOT25	θ _{JA}	250	
Thermal Resistance (Junction to Ambient)	DFN2x2-6		68	
	QFN3x3-16		35	
	TSOT25		400	
Internal Power Dissipation	DFN2x2-6	PD	980	mW
	QFN3x3-16		1470	

Note: 1. The maximum output current for TSOT25 package is limited by internal power dissipation capacity as described in Application Information here inafter.





Electrical Characteristics (@T_A = +25°C, V_{IN} = 3.6V, V_O = 1.8V, C_{IN} = 10µF, C_{OUT} = 10µF, L = 4.7µH, unless otherwise specified.)

Parameter	Symbol	Test C	onditions	Min	Тур	Max	Units
Input Voltage Range	V _{IN}			2.5		5.5	V
Regulated Feedback Voltage	V _{FB}	lo = 100mA		0.588	0.6	0.612	V
Reference Voltage Line Regulation	ΔV_{FB}				0.3		%/V
Regulated Output Voltage Accuracy	Vo	I _O = 100mA		-3		+3	%
Peak Inductor Current	I _{PK}	V _{IN} = 3V,V _{FB} = 0.5V	' or V _O = 90%		1.5		А
Output Voltage Line Regulation	LNR	V_{IN} = 2.5V to 5V, I _C) = 10mA		0.2	0.5	%/V
Output Voltage Load Regulation	LDR	I _O = 1mA to 800mA			1.5		%
Quiescent Current	lq	No load			40	70	μA
Shutdown Current	I _{SD}	V _{EN} = 0V			0.1	1	μA
		V _O = 100%		1.2	1.5	1.8	MHz
Oscillator Frequency	fosc	$V_{FB} = 0V \text{ or } V_O = 0V$			500		kHz
Drain-Source On-State Resistance		I _{DS} = 100mA	P MOSFET		0.3	0.45	Ω
Drain-Source On-State Resistance	R _{DS(ON)}		N MOSFET		0.35	0.5	Ω
SW Leakage Current	ILSW				±0.01	1	μA
EN Threshold High	V _{EH}			1.5			V
EN Threshold Low	V _{EL}					0.3	V
EN Leakage Current	I _{EN}				±0.01		μA
Over Temperature Protection	OTP				150		°C
OTP Hysteresis	OTH				30		°C



b=10mA

- - b=100mA

5.0

b=10mA

— b=100mA

- - - - b=1000mA

5.0

lo=10mA

lo=100mA

- -lo=1000mA

- -

4.5

55

5.5

4.0

40

4.5

4.5

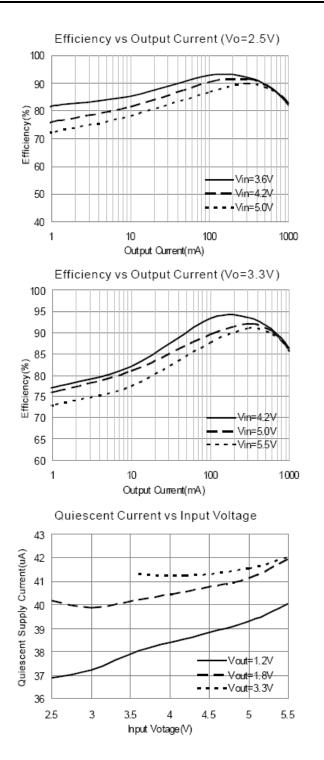
Efficiency vs Output Current (Vo=1.2V) Efficiency vs Input Voltage (Vo=1.2V) 100 95 90 90 85 80 Efficiency(%) Efficiency(%) 80 70 75 60 Vin=3.6V 70 Vin=4.2V 50 -Vin=5.0V 65 -40 60 10 100 1000 1 2.5 3.0 3.5 Input Voltage(V) Output Current(mA) Efficiency vs Output Current (Vo=1.5V) Efficiency vs Input Voltage (Vo=1.5V) 100 95 90 90 85 80 Efficiency(%) Efficiency (%) 02 22 00 70 60 70 Vin=3.6V 50 • Vin=4.2V 65 - - - Vin=5.0V 60 40 2.5 3.0 3.5 1000 1 10 100 Input Voltage(V) Output Current (mA) Eifficiency vs Input Voltage (Vo=1.8V) Efficiency vs Output Current (Vo=1.8V) 95 100 90 90 Efficiency(%) 85 80 80 Efficiency(%) 70 75 60 70 Vin=3.6V 50 Vin=4.2V 65 -Vin=5.0V - -60 40 10 1000 2.5 1 100 3.5 Output Current(mA) Input Voltage(V)

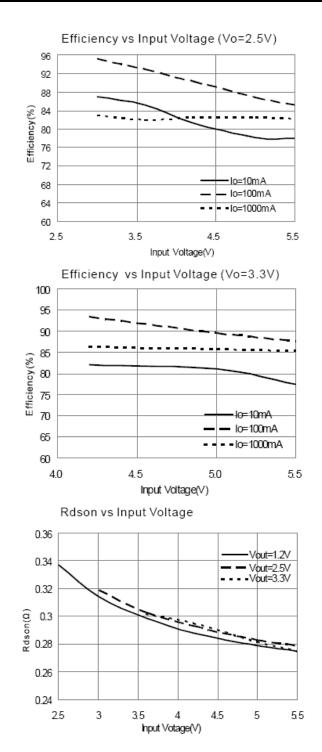
Typical Performance Characteristics (@T_A = +25°C, C_{IN} = 10µF, C_O = 10µF, L = 4.7µH, unless otherwise specified.)

5.5



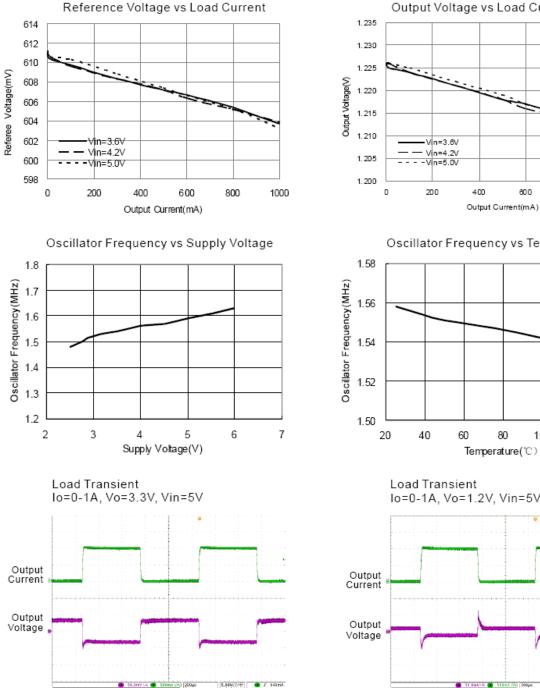
Typical Performance Characteristics (cont.) (@T_A = +25°C, C_{IN} = 10µF, C_O = 10µF, L = 4.7µH, unless otherwise specified.)







Typical Performance Characteristics (cont.) (@T_A = +25°C, C_{IN} = 10µF, C_O = 10µF, L = 4.7µH, unless otherwise specified.)



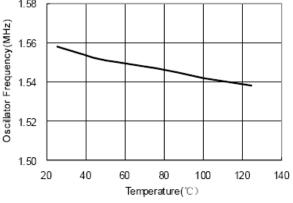
Output Voltage vs Load Current

Oscillator Frequency vs Temperature

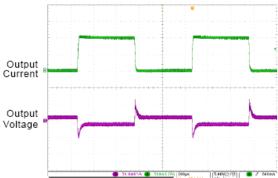
600

800

1000



Io=0-1A, Vo=1.2V, Vin=5V





PAM2305D

Application Information

The basic PAM2305D application circuit is shown in Page 2. External component selection is determined by the load requirement, selecting L first and then C_{IN} and C_{OUT} .

Inductor Selection

For most applications, the value of the inductor will fall in the range of 1μ H to 4.7μ H. Its value is chosen based on the desired ripple current. Large value inductors lower ripple current and small value inductors result in higher ripple currents. Higher V_{IN} or V_{OUT} also increases the ripple current as shown in Equation 1. A reasonable starting point for setting ripple current is Δ I_L = 400mA (40% of 1A).

$$\Delta I_{L} = \frac{1}{(f)(L)} V_{OUT} \left(1 - \frac{V_{OUT}}{V_{IN}} \right)$$
Equation (1)

The DC current rating of the inductor should be at least equal to the maximum load current plus half the ripple current to prevent core saturation. Thus, a 1.4A rated inductor should be enough for most applications (1A + 400mA). For better efficiency, choose a low DC-resistance inductor.

Vo	1.2V	1.5V	1.8V	2.5V	3.3V
L	2.2µH	2.2µH	2.2µH	4.7µH	4.7µH

CIN and COUT Selection

In continuous mode, the source current of the top MOSFET is a square wave of duty cycle V_{OUT}/V_{IN}. To prevent large voltage transients, a low ESR input capacitor sized for the maximum RMS current must be used. The maximum RMS capacitor current is given by:

$$C_{\text{IN}} \text{required } I_{\text{RMS}} \cong I_{\text{OMAX}} \frac{\left[V_{\text{OUT}} \left(V_{\text{IN}} - V_{\text{OUT}}\right)\right]^{1/2}}{V_{\text{IN}}}$$

This formula has a maximum at $V_{IN} = 2V_{OUT}$, where $I_{RMS} = I_{OUT}$ /2. This simple worst-case condition is commonly used for design because even significant deviations do not offer much relief. Note that the capacitor manufacturer's ripple current ratings are often based on 2000 hours of life. This makes it advisable to further derate the capacitor, or choose a capacitor rated at a higher temperature than required. Consult the manufacturer if there is any question.

The selection of C_{OUT} is driven by the required effective series resistance (ESR).

Typically, once the ESR requirement for C_{OUT} has been met, the RMS current rating generally far exceeds the I_{RIPPLE} (P-P) requirement. The output ripple ΔV_{OUT} is determined by:

$$\Delta V_{OUT} \cong \Delta i_L \left(ESR + \frac{1}{8f C_{OUT}} \right)$$

Where f = operating frequency, C_{OUT} = output capacitance and ΔI_L = ripple current in the inductor. For a fixed output voltage, the output ripple is highest at maximum input voltage since ΔI_L increases with input voltage.

Using Ceramic Input and Output Capacitors

Higher values, lower cost ceramic capacitors are now becoming available in smaller case sizes. Their high ripple current, high voltage rating and low ESR make them ideal for switching regulator applications. Using ceramic capacitors can achieve very low output ripple and small circuit size.

When choosing the input and output ceramic capacitors, choose the X5R or X7R dielectric formulations. These dielectrics have the best temperature and voltage characteristics of all the ceramics for a given value and size.

Thermal Consideration

Thermal protection limits power dissipation in the PAM2305D. When the junction temperature exceeds 150°C, the OTP (Over Temperature Protection) starts the thermal shutdown and turns the pass transistor off. The pass transistor resumes operation after the junction temperature drops below +120°C.

For continuous operation, the junction temperature should be maintained below +125°C.

The power dissipation is defined as:

$$P_{D} = I_{O}^{2} \frac{V_{O}R_{DS(ON)H} + (V_{IN} - V_{O}R_{DS(ON)L}}{V_{IN}} + (t_{SW}F_{S}I_{O} + I_{Q})V_{IN}$$

IQ is the step-down converter quiescent current. The term tsw is used to estimate the full load step-down converter switching losses.

PAM2305D
Document number: DS36396 Rev. 3 - 2



Application Information (cont.)

For the condition where the step-down converter is in dropout at 100% duty cycle, the total device dissipation reduces to:

$$P_{\rm D} = I_{\rm O}^2 R_{\rm DS(ON)H} + I_{\rm Q} V_{\rm IN}$$

Since R_{DS(ON)}, quiescent current, and switching losses all vary with input voltage, the total losses should be investigated over the complete input voltage range. The maximum power dissipation depends on the thermal resistance of IC package, PCB layout, the rate of surrounding airflow and temperature difference between junction and ambient. The maximum power dissipation can be calculated by the following formula:

$$P_D = \frac{T_{J(MAX)} - T_A}{\theta_{JA}}$$

Where $T_{J(MAX)}$ is the maximum allowable junction temperature +125°C. T_A is the ambient temperature and θ_{JA} is the thermal resistance from the junction to the ambient. Based on the standard JEDEC for a two layers thermal test board, the thermal resistance θ_{JA} of TSOT25 package is 250°C/W, DFN2X2 102°C/W and QFN3X3 68°C/W, respectively. The maximum power dissipation at $T_A = +25$ °C can be calculated by following formula:

SOT-25 package:

 $P = (125^{\circ}C - 25^{\circ}C)/250^{\circ}C/W = 0.4W$

DFN2*2 package:

P = (125°C - 25°C)/102°C/W = 0.984W

QFN3*3 package:

P = (125°C - 25°C)/68°C/W = 1.47W

Setting the Output Voltage

The internal reference is 0.6V (Typical). The output voltage is calculated as below:

 $V_O = 0.6 \times \left(1 + \frac{R1}{R2}\right)$

The output voltage is given by Table 1.

Table 1:Resistor selection for output voltage setting.						
Vo	R1	R2				
1.2V	100k	100k				
1.5V	150k	100k				
1.8V	200k	100k				
2.5V	380k	120k				
3.3V	540k	120k				

100% Duty Cycle Operation

As the input voltage approaches the output voltage, the converter turns the P-Channel transistor continuously on. In this mode the output voltage is equal to the input voltage minus the voltage drop across the P-Channel transistor:

 $V_{OUT} = V_{IN} - I_{LOAD} (R_{DS(ON)} + R_L)$

where R_{DS(ON)} = P-Channel switch ON resistance, I_{LOAD} = Output current, R_L = Inductor DC resistance.

UVLO and Soft-Start

The reference and the circuit remain reset until the V_{IN} crosses its UVLO threshold.

The PAM2305D has an internal soft-start circuit that limits the in-rush current during start-up. This prevents possible voltage drops of the input voltage and eliminates the output voltage overshoot. The soft-start acts as a digital circuit to increase the switch current in several steps to the P-Channel current limit (1500mA).

Short Circuit Protection

The switch peak current is limited cycle-by-cycle to a typical value of 1500mA. In the event of an output voltage short circuit, the device operates with a frequency of 400kHz and minimum duty cycle, therefore the average input current is typically 200mA.





Application Information (cont.)

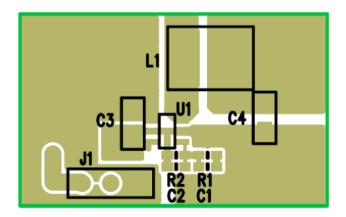
Thermal Shutdown

When the die temperature exceeds +150°C, a reset occurs and the reset remains until the temperature decrease to +120°C, at which time the circuit can be restarted.

PCB Layout Check List

When laying out the printed circuit board, the following checklist should be used to ensure proper operation of the PAM2305D. These items are also illustrated graphically in Figure 1. Check the following in your layout:

- 1. The power traces, consisting of the GND trace, the SW trace and the VIN trace should be kept short, direct and wide.
- 2. Does the V_{FB} pin connect directly to the feedback resistors? The resistive divider R1/R2 must be connected between the (+) plate of C_{OUT} and around.
- 3. Does the (+) plate of C_{IN} connect to V_{IN} as closely as possible? This capacitor provides the AC current to the internal power MOSFETs.
- 4. Keep the switching node, SW, away from the sensitive V_{FB} node.
- 5. Keep the (–) plates of C_{IN} and C_{OUT} as close as possible.



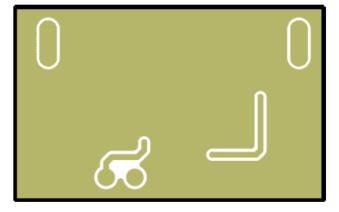
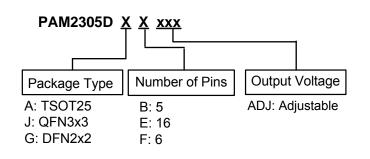


Figure 1. PAM2305D Suggested Layout

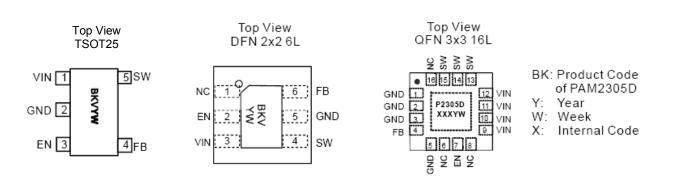


Ordering Information



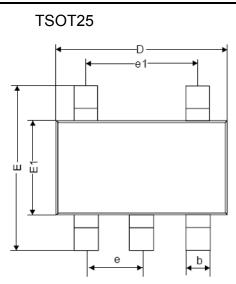
Part Number	Output Voltage	Part Marking	Package Type	Standard Package
PAM2305DABADJ	ADJ	BKAYW	TSOT25	3000 Units/Tape&Reel
PAM2305DJEADJ	ADJ	P2305D	QFN3x3	3000 Units/Tape&Reel
PAM2305DGFADJ	ADJ	BKAYW	DFN2x2-6	3000 Units/Tape&Reel

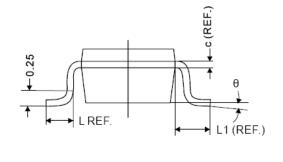
Marking Information

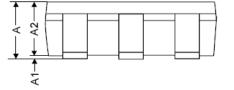




Package Outline Dimensions (All dimensions in mm.)





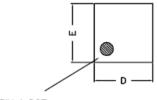


DEE	Millim	eter	
REF.	Min	Max	
А	1.10 M	ΛAX	
A1	0	0.10	
A2	0.70	1	
c	0.12 F	REF.	
D	2.70	3.10	
Е	2.60	3.00	
E1	1.40	1.80	
L	0.45 F	REF.	
L1	0.60 F	REF.	
θ	0°	10º	
b	0.30	0.50	
e	0.95 REF.		
e1	1.90 REF.		



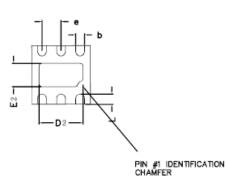
Package Outline Dimensions (cont.) (All dimensions in mm.)

DFN 2x2

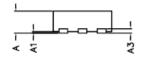








BOTTOM VIEW



SIDE VIEW

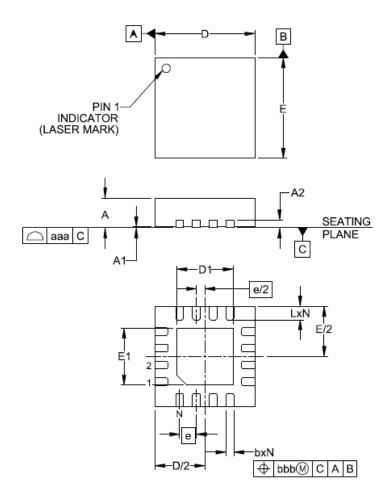
COMMON DIMENSIONS(MM)						
PKG.	W:	VERY VERY	THIN			
REF.	MIN.	NOM.	МАХ			
A	0.70	0.75	0.80			
A1	0.00	—	0.05			
A3	0.2 REF.					
D	1.95	2.00	2.05			
E	1.95	2.00	2.05			
b	0.25	0.30	0.35			
L	0.25	0.35	0.45			
D2	1.35	1.50	1.60			
E2	0.65	0.80	0.90			
е	0.65 BSC					





Package Outline Dimensions (cont.) (All dimensions in mm.)

3x3 mm QFN 16



DIN	DIMENSIONS (Millieters)					
	MIN	ΤYΡ	MAX			
А	0.70	0.75	0.80			
A1	0.00	0.02	0.05			
A2		0.20				
b	0.18	0.25	0.30			
D	2.90	3.00	3.10			
D1	1.55	1.70	1.80			
Е	2.90	3.00	3.10			
E1	1.55	1.70	1.80			
e		0.50BSC	;			
L	0.30	0.40	0.50			
Ν	16					
aaa	0.08					
bbb	0.10					

Notes:

Controlling dimensions are in millimeters (angles in degress).
Coplanarity applies to the exposed pad as well as the terminals.
DAP is 1.90 x 1.90mm.



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